

Features

- \cdot High power gain (PG = 13dB typ; f = 0.4GHz)
- High cutoff frequency ($f_T = 1.2 GHz typ$)
- \cdot Low C_{ob} (C_{ob} = 1.0pF typ).
- · Complementary pair with the 2SC4269

Absolute Maximum Ratings at		unit	
Collector to Base Voltage	V _{CBO}	-15	V
Collector to Emitter Voltage	V _{CEO}	-15	v
Emitter to Base Voltage	VEBO	3	v
Collector Current	IC	- 50	mA
Collector Dissipation	P_{C}	250	mW
Junction Temperature	Тј	150	°C
Storage Temperature	Tstg	-55 to $+150$	°C

Electrical Characteristics at Ta	$=25^{\circ}C$		min	typ	max	unit
Collector Cutoff Current	I _{CBO}	$V_{CB} = -15V, I_E = 0$			-0.1	μA
Emitter Cutoff Current	I _{EBO}	$V_{EB} = -2V, I_C = 0$			-0.1	μA
DC Current Gain	$\mathbf{h_{FE}}$	$V_{CE} = -10V, I_C = -5mA$	40 💥		200×	<
Gain-Bandwidth Product	f_T	$V_{CE} = -10V, I_C = -5mA$	0.6	1.2		GHz
Output Capacitance	Cob	$V_{CB} = -10V$, f = 1MHz		1.0	1.5	pF
Reverse Transfer Capacitance	C_{re}	$V_{CB} = -10V, f = 1MHz$		0.75		pF
Power Gain	PG	$V_{CE} = -10V, I_C = -5mA, f = 0.4GHz$		13		dB
Noise Figure	NF	$V_{CE} = -10V, I_C = -3mA, f = 0.4GHz$		2.5		dB

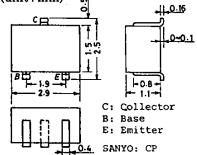
% : The 2SA1778 are classified by 5mA h_{FE} as follows :

40	2	80	60	3	120	100	4	200	

Note

Marking : HS h_{FE} rank : 2,3,4

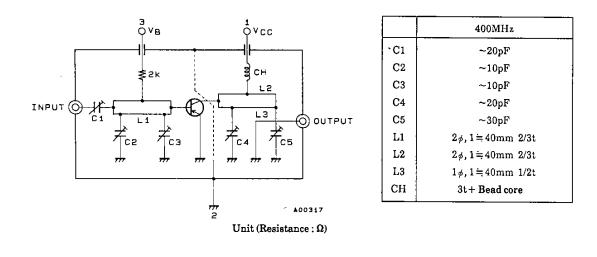
Package Dimensions 2018A (unit:mm)

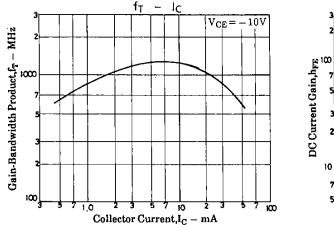


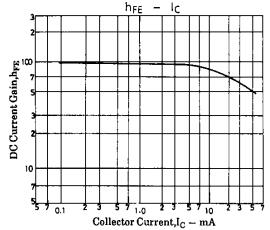
SANYO Electric Co., Ltd. Semiconductor Business Headquarters TOKYO OFFICE Tokyo Bldg., 1-10, 1 Chome, Ueno, Taito-ku, TOKYO, 110 JAPAN

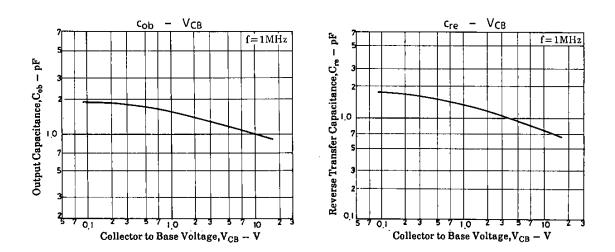
20193YK(KOTO) No.3481-1/5

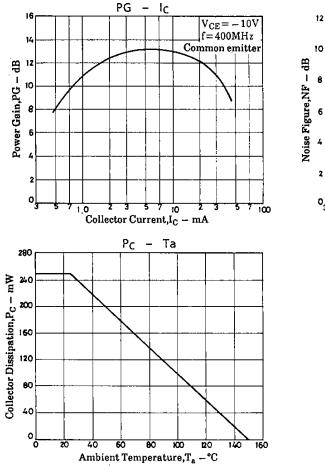
PG, NF Test Circuit

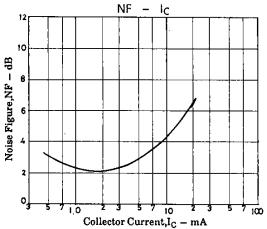






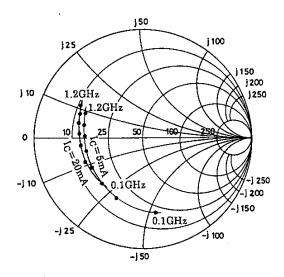




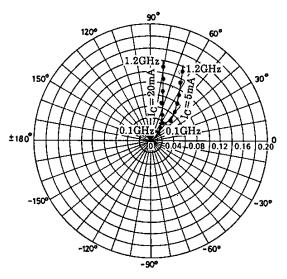


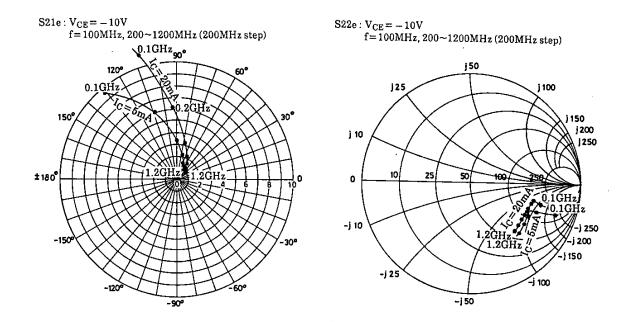


 $\begin{array}{l} S11e: V_{CE} = -10V \\ f = 100 MHz, 200 {\sim} 1200 MHz \mbox{ (200 MHz step)} \end{array}$



 $\begin{array}{c} S12e: V_{CE}\!=\!-10V \\ f\!=\!100MHz, 200\!\sim\!\!1200MHz \, (200MHz \, step) \end{array}$





$\frac{S \text{ Parameter (Common emitter)}}{V_{CE} = -10 \text{V}, I_C = -5 \text{mA}, Zo = 50 \Omega}$

Freq. (MHz)	S ₁₁		S_2	21	S	2	S ₂₂	
	MAG	ANG	MAG	ANG	MAG	ANG	MAG	ANG
100	0.685	- 79.5	9.506	130.8	0.039	55.5	0.770	- 19.6
200	0.594	-117.7	6.031	108.6	0.052	45.9	0.670	-21.2
400	0.554	-154.4	3.349	89.0	0.065	48.3	0.599	- 22.8
600	0.551	-170.6	2.331	76.1	0.079	53.9	0.579	- 26.4
800	0.555	179.4	1.823	65.9	0.095	58.8	0.575	- 31.4
1000	0.568	169.6	1.496	57.0	0.112	62.5	0.576	- 37.3
1200	0.581	162.5	1.292	48.9	0.132	65.8	0.579	- 43.6

 $V_{CE} = -10V$, $I_C = -20mA$, $Z_0 = 50\Omega$

Freq (MHz)	s	S ₁₁		S ₂₁		2	S ₂₂	
	MAG	ANG	MAG	ANG	MAG	ANG	MAG	ANG
100	0.566	-134.4	11.446	110.0	0.022	51.6	0.660	- 16.2
200	0.579	- 159.2	6.160	92.9	0.030	56.4	0.600	- 14.3
400	0.599	-175.8	3.152	77.2	0.047	66.3	0.586	-16.4
600	0.613	174.8	2.128	65.9	0.066	71.2	0.591	-21.4
800	0.632	167.3	1.618	56.4	0.084	75.3	0.601	-27.8
1000	0.645	160.0	1.305	47.6	0.106	77.8	0.610	- 34.7
1200	0.663	153.9	1.097	40.4	0.130	79.9	0.620	- 42.0

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